ALPHA & OMEGA SEMICONDUCTOR

AOTF10N50FD

500V, 10A N-Channel MOSFET with Fast Recovery Diode

General Description

The AOTF10N50FD has been fabricated using an advanced high voltage MOSFET process that is designed to deliver high levels of performance and robustness in popular AC-DC applications. By providing low $R_{DS(on)}$, C_{iss} and C_{rss} along with guaranteed avalanche capability this part can be adopted quickly into new and existing offline power supply designs.

Product Summary

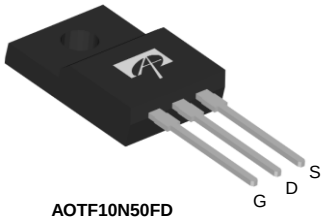
V_{DS}	600V@150℃
I_D (at V_{GS}=10V)	10A
$R_{DS(ON)}$ (at V_{GS}=10V)	< 0.75Ω

100% UIS Tested
100% R_g Tested

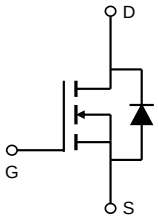
Green Product

Top View

TO-220F



AOTF10N50FD



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	AOTF10N50FD	Units
Drain-Source Voltage		V_{DS}	500	V
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current	T_C=25°C	I_D	10*	A
	T_C=100°C		6*	
Pulsed Drain Current [C]		I_{DM}	33	
Avalanche Current [C]		I_{AR}	3.8	A
Repetitive avalanche energy [C]		E_{AR}	216	mJ
Single pulsed avalanche energy [G]		E_{AS}	433	mJ
Peak diode recovery dv/dt		dv/dt	5	V/ns
Power Dissipation [B]	T_C=25°C	P_D	50	W
	Derate above 25°C		0.4	W/ °C
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds		T_L	300	°C

Thermal Characteristics

Parameter	Symbol	AOT10N50FD	Units
Maximum Junction-to-Ambient [A,D]	$R_{\theta JA}$	65	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	2.5	°C/W

* Drain current limited by maximum junction temperature.

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=10mA, V_{GS}=0V, T_J=25°C	500			V
		I_D=10mA, V_{GS}=0V, T_J=150°C		600		
BV_{DSS} /ΔTJ	Breakdown Voltage Temperature Coefficient	I_D=10mA, V_{GS}=0V		0.56		V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=500V, V_{GS}=0V			10	μA
		V_{DS}=400V, T_J=125°C			100	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±30V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=5V, I_D=250μA	2.5	3.1	4.2	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=5A		0.6	0.75	Ω
g_{FS}	Forward Transconductance	V_{DS}=40V, I_D=5A		10		S
V_{SD}	Diode Forward Voltage	I_S=10A,V_{GS}=0V		0.93	1.6	V
I_S	Maximum Body-Diode Continuous Current				10	A
I_{SM}	Maximum Body-Diode Pulsed Current				33	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=25V, f=1MHz	820	1030	1240	pF
C_{oss}	Output Capacitance		75	112	150	pF
C_{rss}	Reverse Transfer Capacitance		5	10	15	pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	1.7	3.4	5.2	Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=400V, I_D=10A	20	26	35	nC
Q_{gs}	Gate Source Charge			4.8		nC
Q_{gd}	Gate Drain Charge			9.5		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=250V, I_D=10A, R_G=25Ω		24		ns
t_r	Turn-On Rise Time			65		ns
$t_{D(off)}$	Turn-Off DelayTime			69		ns
t_f	Turn-Off Fall Time			50		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=10A,dI/dt=100A/μs,V_{DS}=100V		116	190	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=10A,dI/dt=100A/μs,V_{DS}=100V		0.3	0.6	μC

A. The value of $R_{\theta JA}$ is measured with the device in a still air environment with T_A=25° C.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150° C, Ratings are based on low frequency and duty cycles to keep initial T_J =25° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.
G. L=60mH, I_{AS}=3.8A, V_{DD}=150V, R_G=25Ω, Starting T_J=25° C

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

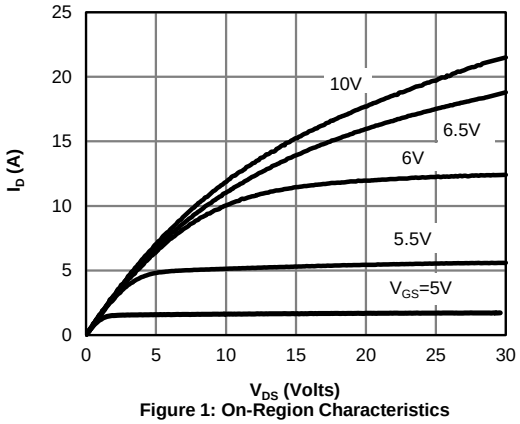


Figure 1: On-Region Characteristics

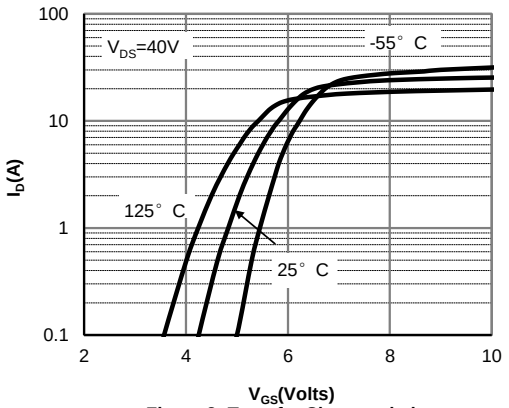


Figure 2: Transfer Characteristics

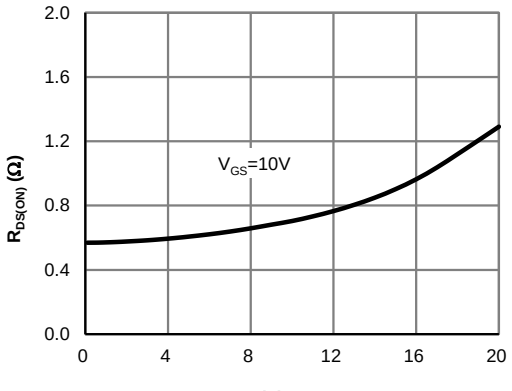


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

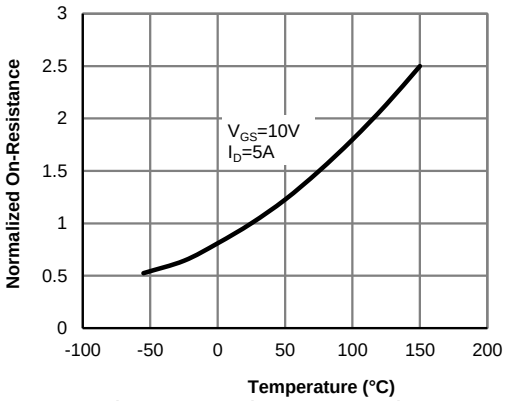


Figure 4: On-Resistance vs. Junction Temperature

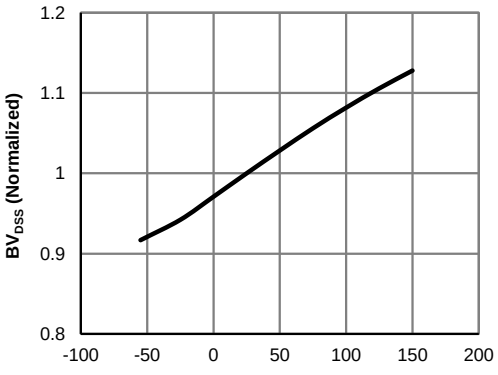


Figure 5: Break Down vs. Junction Temperature

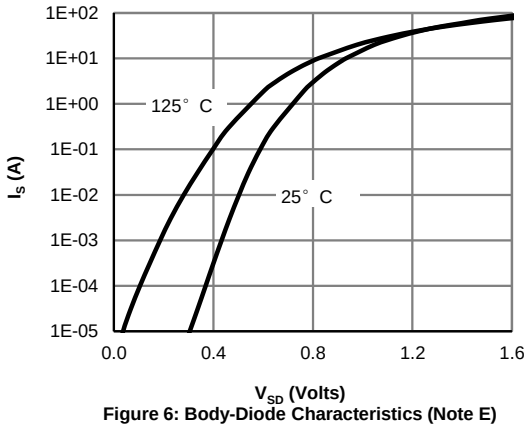


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

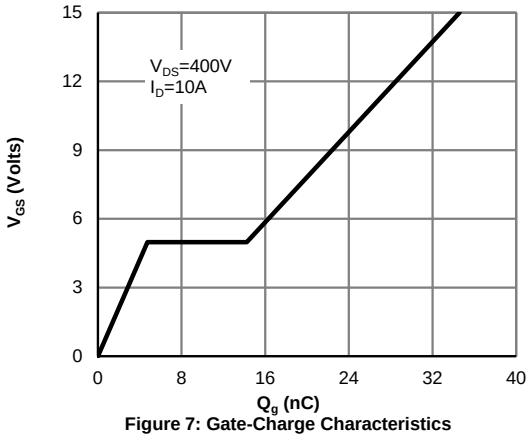


Figure 7: Gate-Charge Characteristics

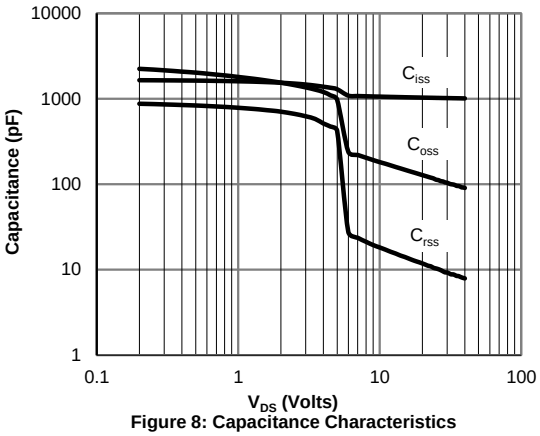


Figure 8: Capacitance Characteristics

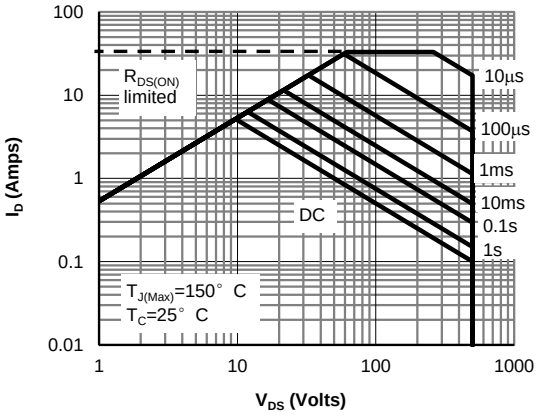


Figure 9: Maximum Forward Biased Safe Operating Area for AOTF10N50FD (Note F)

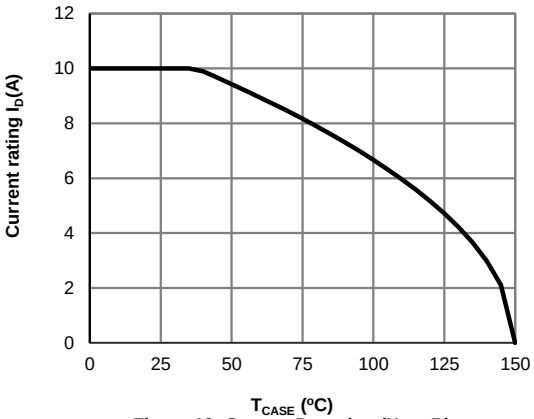


Figure 10: Current De-rating (Note B)

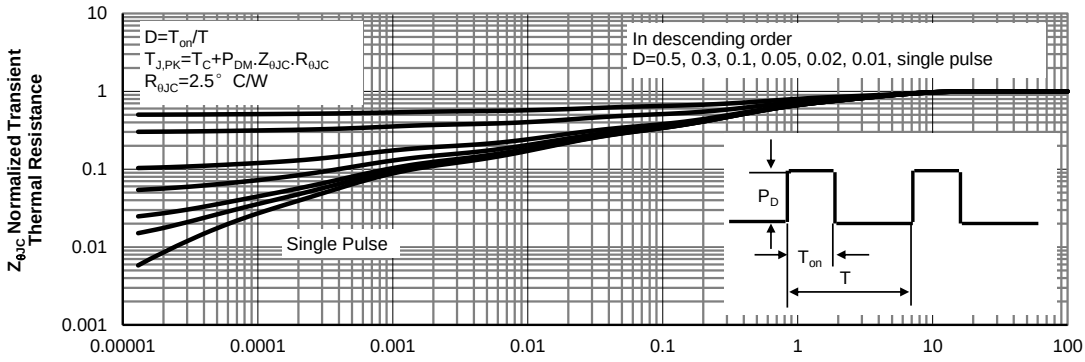


Figure 11: Normalized Maximum Transient Thermal Impedance for AOTF10N50FD (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

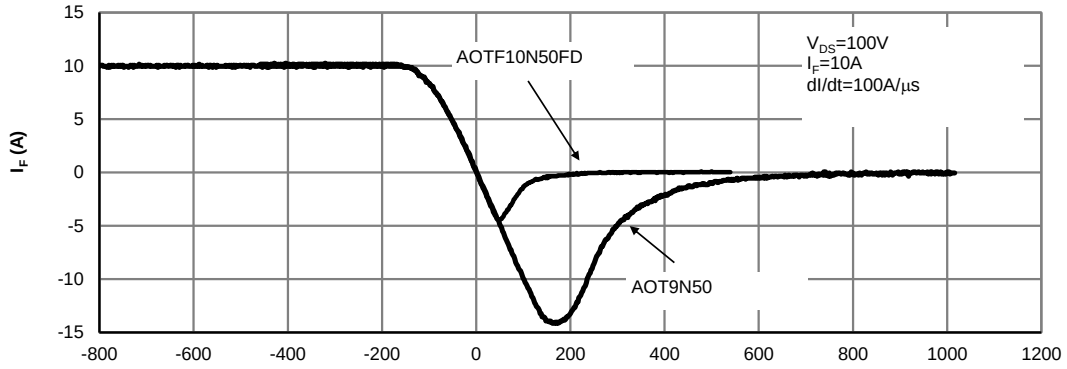
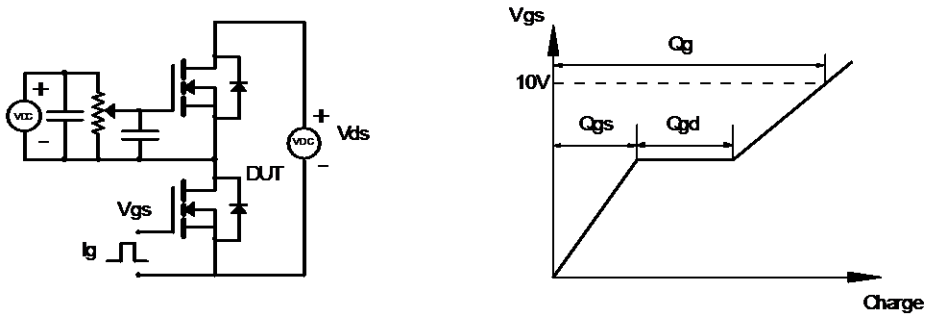
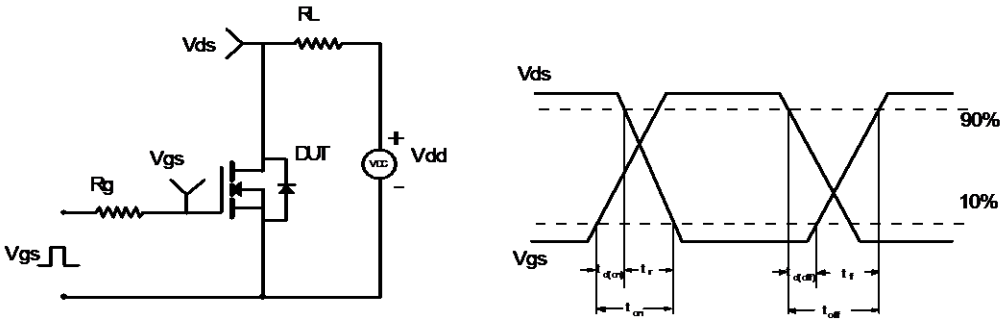


Figure 12: Diode Recovery Characteristics

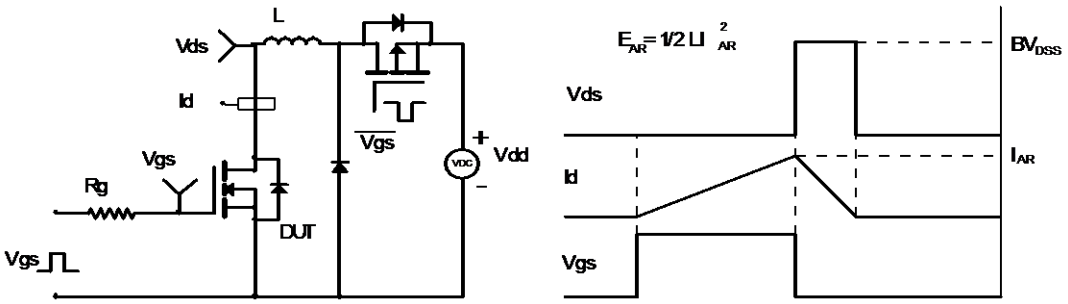
Gate Charge Test Circuit & Waveform



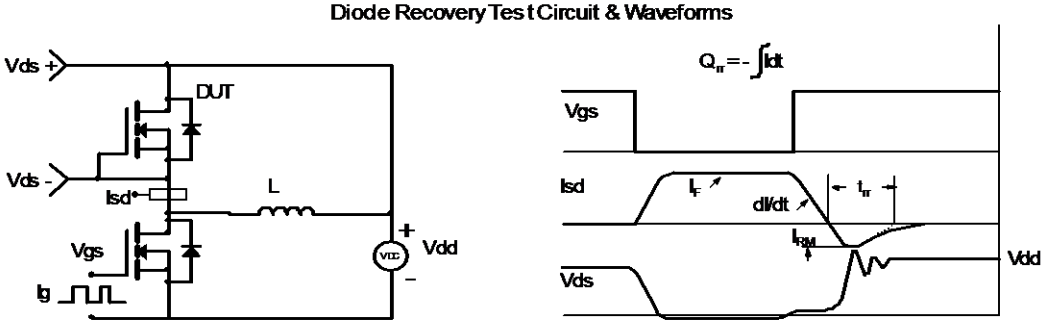
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



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